

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S107	11	((fin with (mosfet or misfet or igfet or fet or transistor)) or fin\$1fet) same fermi)	US-PGPUB; USPAT	OR	ON	2005/11/08 12:16
S105	9	S104 and (@ad<"20040319" or @rlad<"20040319")	US-PGPUB; USPAT	OR	ON	2005/11/08 12:16
S108	9	S107 and (@ad<"20040319" or @rlad<"20040319")	US-PGPUB; USPAT	OR	ON	2005/11/08 12:22
S113	41	S112 and ( (gate adj (oxide or dielectric or insulator or insulating or insulation)) with (thickness with (thick or thicker or higher or lower or greater or thinner or thin)) )	US-PGPUB; USPAT	OR	ON	2005/11/08 12:24
S115	114	finfet	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/08 12:30
S118	0	S116 and ( (gate adj (oxide or dielectric or insulator or insulating or insulation)) with thickness )	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/08 12:31
S117	0	S116 and ( (gate adj (oxide or dielectric or insulator or insulating or insulation)) with (thickness near different) )	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/08 12:31
S119	2	S116 and ( (gate adj (oxide or dielectric or insulator or insulating or insulation)) )	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/08 12:32
S112	360	S111 and (@ad<"20040319" or @rlad<"20040319")	US-PGPUB; USPAT	OR	ON	2005/11/08 12:33
S111	421	finfet	US-PGPUB; USPAT	OR	ON	2005/11/08 12:33
S125	3	S124 not S114	US-PGPUB; USPAT	OR	ON	2005/11/08 12:34
S114	18	S112 and ( (gate adj (oxide or dielectric or insulator or insulating or insulation)) with (thickness near different) )	US-PGPUB; USPAT	OR	ON	2005/11/08 12:34
S128	23	S127 and (@pd<"20040319")	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/08 12:42
S127	170	(finfet or fin\$1fet or (fin adj field adj effect))	EPO; JPO; DERWENT	OR	ON	2005/11/08 12:42
S126	3	S123 and ( (gate adj (oxide or dielectric or insulator or insulating or insulation)) with (thickness near (higher or lower)) )	US-PGPUB; USPAT	OR	ON	2005/11/08 12:42

S11 6	15	S115 and (@pd<"20040319")	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/08 12:42
S12 9	0	S128 and ( (gate adj (oxide or dielectric or insulator or insulating or insulation)) with (thickness near (higher or lower or different)) )	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/08 12:43
S13 2	19	S131 not S130	US-PGPUB; USPAT	OR	ON	2005/11/08 12:44
S13 1	29	S122 and (@ad<"20010319" )	US-PGPUB; USPAT	OR	ON	2005/11/08 12:44
S13 0	10	S122 and (@ad<"20000319" )	US-PGPUB; USPAT	OR	ON	2005/11/08 12:44
S12 2	478	(finfet or fin\$1fet or (fin adj field adj effect))	US-PGPUB; USPAT	OR	ON	2005/11/08 14:07
S13 7	0	S135 and ( (gate adj (oxide or dielectric or insulator or insulating or insulation)) with (thickness near2 different) )	US-PGPUB; USPAT	OR	ON	2005/11/08 14:08
S13 6	0	S135 and ( (gate adj (oxide or dielectric or insulator or insulating or insulation)) with (thickness near different) )	US-PGPUB; USPAT	OR	ON	2005/11/08 14:08
S12 3	398	S122 and (@ad<"20040319" or @rlad<"20040319")	US-PGPUB; USPAT	OR	ON	2005/11/08 14:08
S14 0	0	((multiple or plurality) adj (finfet or fin\$1fet or (fin adj field adj effect) or (fin adj type) or fin\$1type) ) with voltage)	US-PGPUB; USPAT	OR	ON	2005/11/08 14:11
S13 9	0	((multiple or plurality) adj (finfet or fin\$1fet or (fin adj field adj effect) or (fin adj type) or fin\$1type) ) with threshold)	US-PGPUB; USPAT	OR	ON	2005/11/08 14:11
S13 5	48	S134 and (@ad<"20040319" or @rlad<"20040319")	US-PGPUB; USPAT	OR	ON	2005/11/08 14:11
S14 3	5	((finfet or fin\$1fet or (fin adj field adj effect) or (fin adj type) or fin\$1type) with different with voltage)	US-PGPUB; USPAT	OR	ON	2005/11/08 14:12
S14 1	7	((multiple or plurality) adj (finfet or fin\$1fet or (fin adj field adj effect) or (fin adj type) or fin\$1type) ) with different)	US-PGPUB; USPAT	OR	ON	2005/11/08 14:12
S14 2	7	S141 and (@ad<"20040319" or @rlad<"20040319")	US-PGPUB; USPAT	OR	ON	2005/11/08 14:13
S14 6	5	((finfet or fin\$1fet or (fin adj field adj effect) or (fin adj type) or fin\$1type) with different with thicknesses)	US-PGPUB; USPAT	OR	ON	2005/11/08 14:14

S14 5	4	S144 and (@ad<"20040319" or @rlad<"20040319")	US-PGPUB; USPAT	OR	ON	2005/11/08 14:14
S14 4	5	((finfet or fin\$1fet or (fin adj field adj effect) or (fin adj type) or fin\$1type) with different with voltage)	US-PGPUB; USPAT	OR	ON	2005/11/08 14:14
S13 4	49	((multiple or plurality) adj (finfet or fin\$1fet or (fin adj field adj effect) or (fin adj type) or fin\$1type) )	US-PGPUB; USPAT	OR	ON	2005/11/08 14:16
S15 0	0	((several) adj (finfet or fin\$1fet or (fin adj field adj effect) or (fin adj type) or fin\$1type) with ("same" adj (chip or substrate or surface or wafer)))	US-PGPUB; USPAT	OR	ON	2005/11/08 14:17
S14 8	4	((multiple or plurality) adj (finfet or fin\$1fet or (fin adj field adj effect) or (fin adj type) or fin\$1type) with ("same" adj (chip or substrate or surface or wafer)))	US-PGPUB; USPAT	OR	ON	2005/11/08 14:17
S14 7	4	S146 and (@ad<"20040319" or @rlad<"20040319")	US-PGPUB; USPAT	OR	ON	2005/11/08 14:17
S15 4	7	S153 and ( (gate adj (oxide or dielectric or insulator or insulating or insulation)) with (thickness or thick or thicker or thinner))	US-PGPUB; USPAT	OR	ON	2005/11/08 14:18
S15 3	13	S152 not S149	US-PGPUB; USPAT	OR	ON	2005/11/08 14:18
S15 1	17	( (finfet or fin\$1fet or (fin adj field adj effect) or (fin adj type) or fin\$1type) with ("same" adj (chip or substrate or surface or wafer)))	US-PGPUB; USPAT	OR	ON	2005/11/08 14:18
S14 9	4	S148 and (@ad<"20040319" or @rlad<"20040319")	US-PGPUB; USPAT	OR	ON	2005/11/08 14:18
S13 8	4	S135 and ( (gate adj (oxide or dielectric or insulator or insulating or insulation)) with (thickness or thick or thicker or thinner))	US-PGPUB; USPAT	OR	ON	2005/11/08 14:18
S12 4	21	S123 and ( (gate adj (oxide or dielectric or insulator or insulating or insulation)) with (thickness near different) )	US-PGPUB; USPAT	OR	ON	2005/11/08 14:23
S15 8	0	( (fin near "each") with (gate adj (oxide or dielectric or insulator or insulating or insulation)) )	US-PGPUB; USPAT	OR	ON	2005/11/08 14:24
S15 7	0	( (fin near "each") with (gate adj (oxide or dielectric or insulator or insulating or insulation)) with (thick or thin or thickness) )	US-PGPUB; USPAT	OR	ON	2005/11/08 14:24

S15 6	0	( (fin near "each") with (gate adj (oxide or dielectric or insulator or insulating or insulation)) with (thickness with different) )	US-PGPUB; USPAT	OR	ON	2005/11/08 14:24
S16 2	2	"6921982"	US-PGPUB; USPAT	OR	ON	2005/11/11 12:23
S16 6	18	S165 not S161	US-PGPUB; USPAT	OR	ON	2005/11/11 12:37
S16 4	30	("20030151077" "20030178670" "20040174734" "20040219722" "20050017377" "20050023619" "20050029583" "20050051812" "6391695" "6433609" "6888199")	US-PGPUB; USPAT	OR	ON	2005/11/11 12:37
S16 1	11	("20030151077" "20030178670" "20040174734" "20040219722" "20050017377" "20050023619" "20050029583" "20050051812" "6391695" "6433609" "6888199").PN.	US-PGPUB; USPAT	OR	ON	2005/11/11 12:37
S15 2	17	S151 and (@ad<"20040319" or @riad<"20040319")	US-PGPUB; USPAT	OR	ON	2005/11/11 12:37
S16 3	10	S161 and ( dual\$1gated or double\$1gated or two\$1gated or twin\$1gated or ((dual or double or two or twin) adj (gate or gated or electrode)) or dual\$1gate or double\$1gate or two\$1gate or twin\$1gate or dual\$1electrode or double\$1electrode or two\$1electrode or twin\$1electrode)	US-PGPUB; USPAT	OR	ON	2005/11/11 12:38
S15 5	0	( (fin near "each") with (gate adj (oxide or dielectric or insulator or insulating or insulation)) with (thickness near different) )	US-PGPUB; USPAT	OR	ON	2005/11/11 12:39
S17 1	0	S170 and ( (gate adj (oxide or dielectric or insulator or insulating or insulation)) with thickness )	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/11 13:01
S17 0	7	S169 and (@pd<"20040319")	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/11 13:01

S16 9	37	( fin\$1fet or (fin adj fet) or (fin adj field adj effect) or (fin adj type) or fin\$1type) and ( dual\$1gated or double\$1gated or two\$1gated or twin\$1gated or ((dual or double or two or twin) adj (gate or gated or electrode)) or dual\$1gate or double\$1gate or two\$1gate or twin\$1gate or dual\$1electrode or double\$1electrode or two\$1electrode or twin\$1electrode) and (@ad<"20040319" or @rlad<"20040319")	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/11 13:01
S16 8	20	S167 and ( (gate adj (oxide or dielectric or insulator or insulating or insulation)) with (thickness near different) )	US-PGPUB; USPAT	OR	ON	2005/11/11 13:01
S16 7	394	( fin\$1fet or (fin adj fet) or (fin adj field adj effect) or (fin adj type) or fin\$1type) and ( dual\$1gated or double\$1gated or two\$1gated or twin\$1gated or ((dual or double or two or twin) adj (gate or gated or electrode)) or dual\$1gate or double\$1gate or two\$1gate or twin\$1gate or dual\$1electrode or double\$1electrode or two\$1electrode or twin\$1electrode) and (@ad<"20040319" or @rlad<"20040319")	US-PGPUB; USPAT	OR	ON	2005/11/11 13:01
S16 5	28	S164 and (@ad<"20040319" or @rlad<"20040319")	US-PGPUB; USPAT	OR	ON	2005/11/11 13:01